DET 2 9 2003 NEORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO. MICRON.098DV1	APPLICATION NO. 09/971,955
BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)	APPLICANT Basceri et al.	
(USE SEVERAL SHEETS IF NECESSARY)	FILING DATE October 4, 2001	GROUP 2811

			U.S. PATENT DOCUMENTS			
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
a	5,185,689	02/09/93	Maniar			
a	5,406,445	04/11/95	Fujii et al.			
a	5,581,436	12/03/96	Summerfelt et al.			
Ca	5,781,404	07/14/98	Summerfelt et al.			
an	5,822,175	10/13/98	Azuma			
Ou	6,238,966	05/29/01	Ueda et al.			
a	6,277,436	08/21/01	Stauf et al.			
a	6,319,764	11/20/01	Basceri et al.			
an	6,339,527	01/15/02	Farooq et al.	1		

			FOREIGN PATENT DOCUMENTS				
EXAMINER	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
INITIAL				YES	NO		
							_
		V					

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)				
	· · · · · · · · · · · · · · · · · · ·				

H:\DOCS\SHL\SHL-8893.DOC 122303

EXAMINER	no a	DATE CONSIDERED	7-18-04
*EXAMINER: INITIAL IF CIT	TATION CONSIDERED, WHETHER OR NOT CITATI OT CONSIDERED, INCLUDE COPY OF THIS FORM	ON IS IN CONFORMANCE WITH ME WITH NEXT COMMUNICATION TO	PEP 609; DRAW LINE THROUGH CITATION IF NOT APPLICANT.

			SHEET 1 OF
	FORMATO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.098DV1	APPLICATION NO. 08/971,955
	NIN 0:1 20 NFO MATION DISCLOSURE STATEMENT BY APPLICANT	APPLICANT Basceri et al.	
٠(	PADE NOSE SEVERAL SHEETS IF NECESSARY)	FILING DATE October 4, 2001	GROUP 2811

				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
on	1	6,285,051	09/04/01	Ueda et al.	257	298	
on	2	6,339,527	01/15/02	Farooq et al.	361	305	

				FOREIGN PATENT DOCUMENTS	_			
EXAMINER		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	LATION
INITIAL			1				YES	NO
a	3	WO95/25340	09/21/95	PCT				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
an	Joo, "Fabrication and Characterization of MOCVD (Ba, Sr)TiO3 Thin Films for High Density Capacitors", Proceeding of 1997 5th International Conference an VLSI and CAD", The Secretariat of ICVC '97, 1997.

O:\DOCS\LJM\LJM-3811.DOC 050604

EXAMINER DATE CONSIDERED 7-18-04

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 608; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.